

**Amendments to the Specification**

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*At page 1, line 1; insert the following new paragraph after the title:*

This application is a divisional of co-pending Application No. 10/218,601, filed on August 15, 2002, now U.S. Patent No. 6,620,216 B2, the entire contents of which are hereby incorporated by reference and for which priority is claimed under 35 U.S.C. §120; and this application claims priority under 35 U.S.C. §119 to Application No. 2001-250346, filed in JAPAN on August 21, 2001.

**Amendments to the Claims**

1. **(Currently Amended)** A process for reducing the amount of fine scratches imparted to a substrate during a polishing operation, comprising polishing a substrate to be polished with a polishing composition comprising an abrasive having an average primary particle size of 200 nm or less, an oxidizing agent, an acid having a pK1 of 2 or less and/or a salt of an acid having a pK1 of 2 or less, and water, wherein the acid having a pK1 of 2 or less and/or the salt of an acid having a pK1 of 2 or less is selected from the group consisting of persulfuric acid, pyrophosphoric acid and tripolyphosphoric acid, and wherein the acid value (Y) of the polishing composition is 20 mg KOH/g or less and 0.2 mg KOH/g or more and satisfies the formula (1):

$$\underline{Y \text{ (mg KOH/g)} \leq 5.7 \times 10^{-17} \times X \text{ (/g)} + 19.45} \quad (1)$$

wherein X is a concentration of the abrasive in the polishing composition on a numerical basis.

2-5. **(Cancelled)**

6. **(Currently Amended)** A method for manufacturing a substrate, comprising the step of polishing a substrate to be polished during a manufacturing process with ~~the polishing composition of any one of claims 1 to 2~~ a polishing composition comprising an abrasive having an average primary particle size of 200 nm or less, an oxidizing agent, an acid having a pK1 of 2 or less and/or a salt of an acid having a pK1 of 2 or less, and water, wherein the acid having a pK1 of 2 or less and/or the salt of an acid having a pK1 of 2 or less is selected from the group consisting of persulfuric acid, pyrophosphoric acid and tripolyphosphoric acid, and wherein the acid value (Y) of

the polishing composition is 20 mg KOH/g or less and 0.2 mg KOH/g or more and satisfies the formula (1):

$$Y \text{ (mg KOH/g)} \leq 5.7 \times 10^{-17} \times X \text{ (/g)} + 19.45 \quad (1)$$

wherein X is a concentration of the abrasive in the polishing composition on a numerical basis.

7. (Cancelled)

8. (NEW) The process for reducing the amount of fine scratches imparted to a substrate during a polishing operation according to claim 1, wherein the polishing composition has an acid value (Y) in the range of 0.2 mg KOH/g through 5 mg KOH/g.

9. (NEW) The method for manufacturing a substrate according to claim 6, wherein the polishing composition has an acid value (Y) in the range of 0.2 mg KOH/g through 5 mg KOH/g.